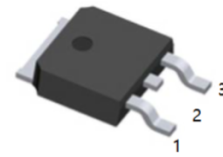


**Applications**

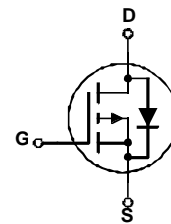
- Inverter
- Power Supplies

**Features**

- $V_{DSS} = -30V$
- $R_{DS(ON)} = 11.6m\Omega (V_{GS} = -10 V)$
- $R_{DS(ON)} = 18m\Omega (V_{GS} = -4.5 V)$
- High performance trench technology for extremely low  $R_{DS(ON)}$
- RoHS Compliant



1.G 2.D 3.S  
TO-252(DPAK) top view



**Absolute Maximum Ratings**  $T_A=25^\circ C$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{DS(Avalanche)}$	Drain-Source Avalanche Voltage (maximum) (Note 4)	-40	V
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V
$I_D$	Continuous Drain Current @ $T_C=25^\circ C$ (Note 3)	@ $T_A=25^\circ C$ (Note 1a)	-55
		Pulsed (Note 1a)	-13
			-100
$P_D$	Power Dissipation @ $T_C=25^\circ C$ (Note 3)	@ $T_A=25^\circ C$ (Note 1a)	57
		@ $T_A=25^\circ C$ (Note 1b)	3.1
			1.3
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

**Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	2.2	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

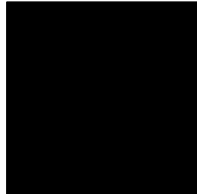
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$E_{AS}$	Drain-Source Avalanche Energy (Single Pulse)	$V_{DD} = -35\text{ V}, I_D = -11\text{ A}, L=1\text{mH}$		61		mJ
$I_{AS}$	Drain-Source Avalanche Current			-14		A
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
$I_{BSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -28\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1	-1.6	-3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -14\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -11\text{ A}$		9.7 14.4	11.6 18	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -14\text{ A}$		35		S
$C_{iss}$	Input Capacitance	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		2370		pF
$C_{oss}$	Output Capacitance			470		pF
$C_{rss}$	Reverse Transfer Capacitance			250		pF
$R_G$	Gate Resistance	$f = 1.0\text{ MHz}$		3.6		$\Omega$
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -20\text{ V}, I_D = -1\text{ A}, V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		18	32	ns
$t_r$	Turn-On Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			62	100	ns
$t_f$	Turn-Off Fall Time			36	58	ns
$Q_g$	Total Gate Charge, $V_{GS} = -10\text{V}$	$V_{DS} = -20\text{ V}, I_D = -14\text{ A}$		45	63	nC
$Q_g$	Total Gate Charge, $V_{GS} = -5\text{V}$			25	35	nC
$Q_{gs}$	Gate-Source Charge			7		nC
$Q_{gd}$	Gate-Drain Charge			10		nC

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -14\text{ A}$ (Note 2)		-0.8	-1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = -14\text{ A}, diF/dt = 100\text{ A}/\mu\text{s}$		28		ns
$Q_{rr}$	Diode Reverse Recovery Charge			15		nC

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $R_{\theta JA} = 40^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $R_{\theta JA} = 96^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

3. Maximum current is calculated as: 
$$\sqrt{\frac{P_D}{R_{DS(ON)}}}$$

where  $P_D$  is maximum power dissipation at  $T_C = 25^\circ\text{C}$  and  $R_{DS(on)}$  is at  $T_{J(max)}$  and  $V_{GS} = 10\text{V}$ . Package current limitation is 21A

4. BV(avalanche) Single-Pulse rating is guaranteed if device is operated within the UIS SOA boundary of the device.

Typical Characteristics

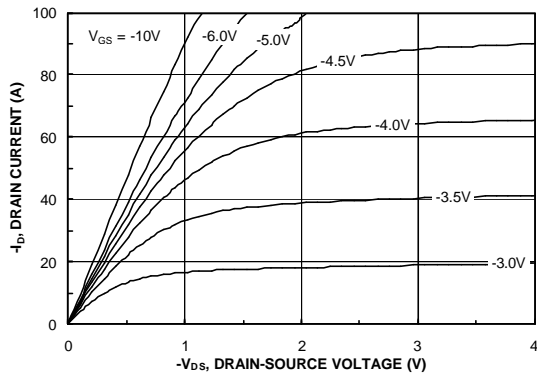


Figure 1. On-Region Characteristics

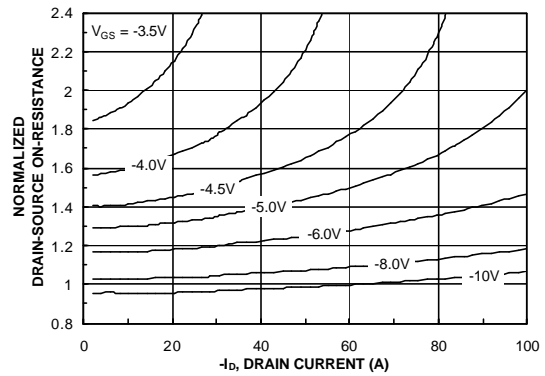


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

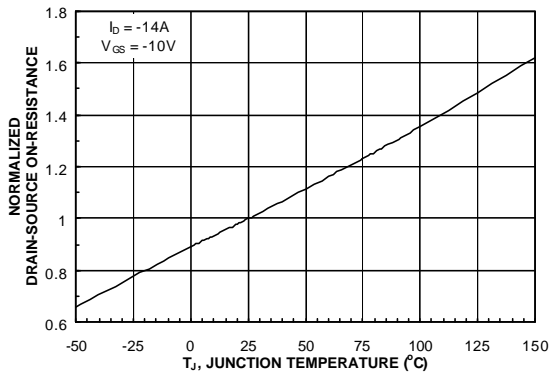


Figure 3. On-Resistance Variation with Temperature

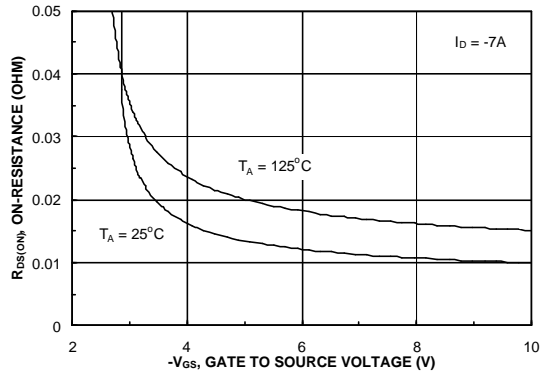


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

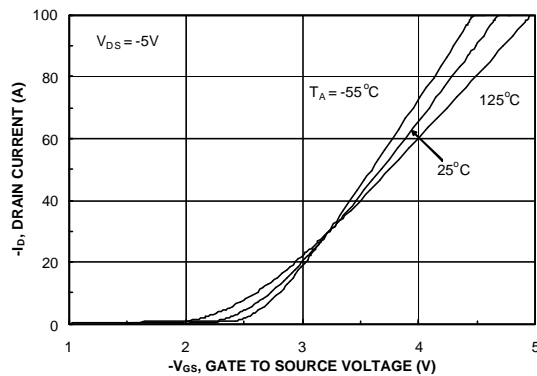


Figure 5. Transfer Characteristics

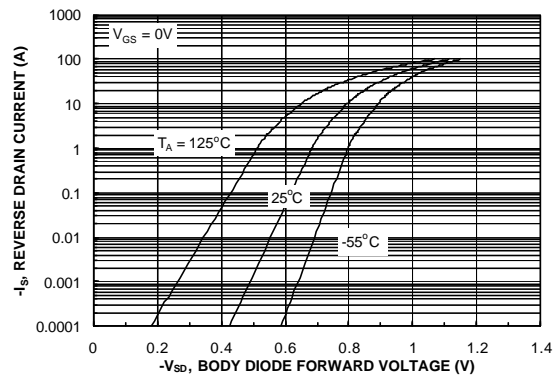


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics

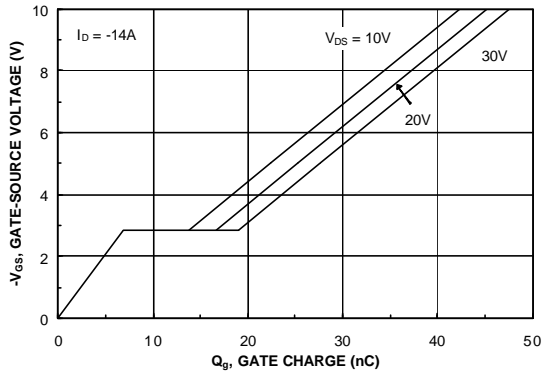


Figure 7. Gate Charge Characteristics

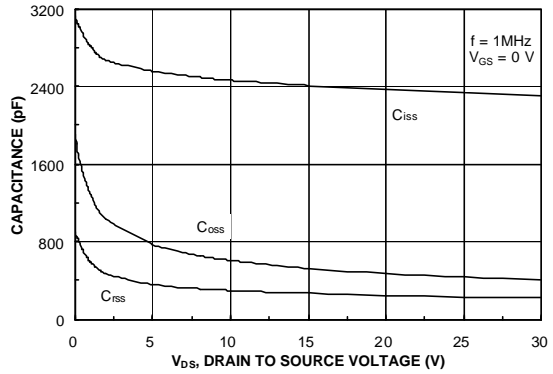


Figure 8. Capacitance Characteristics

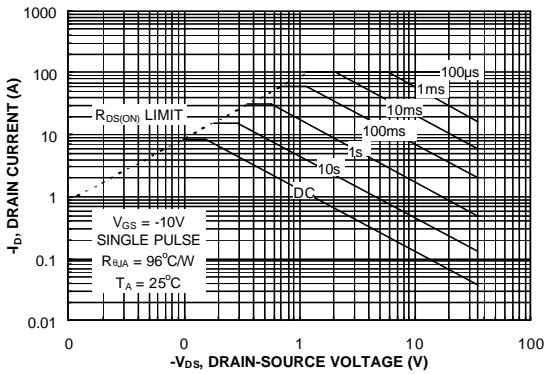


Figure 9. Maximum Safe Operating Area

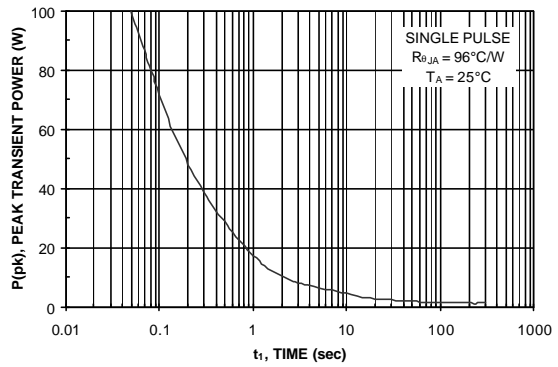


Figure 10. Single Pulse Maximum Power Dissipation

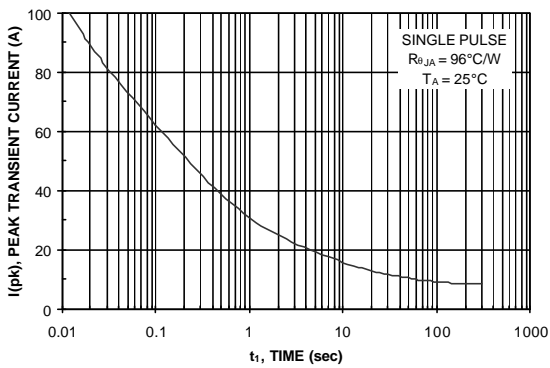


Figure 11. Single Pulse Maximum Peak Current

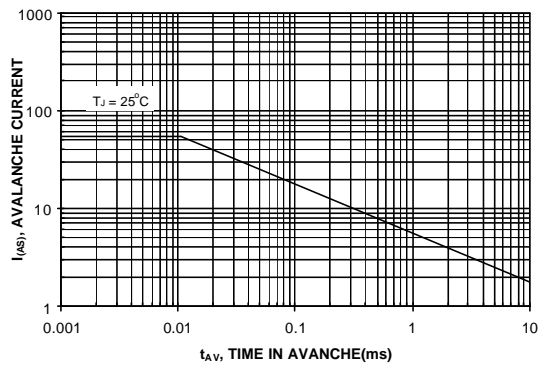
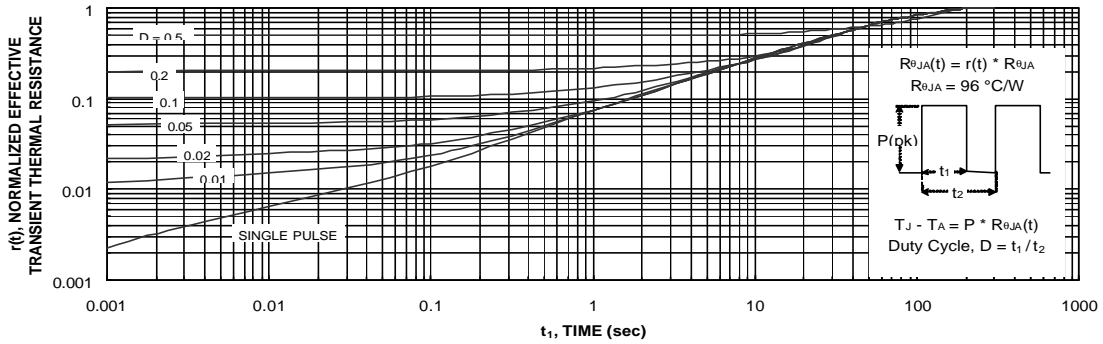


Figure 12. Unclamped Inductive Switching Capability

Typical Characteristics



**Figure 13. Transient Thermal Response Curve**

Thermal characterization performed using the conditions described in Note 1b.  
Transient thermal response will change depending on the circuit board design.

Test Circuits and Waveforms

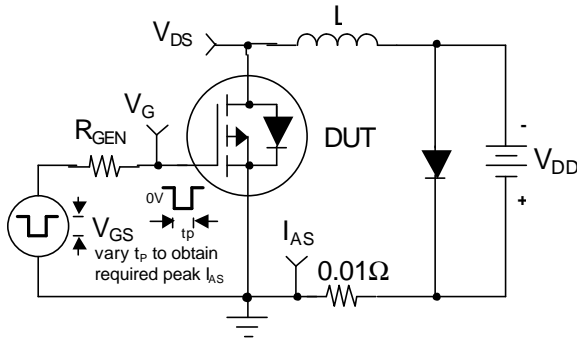


Figure 14. Unclamped Inductive Load Test Circuit

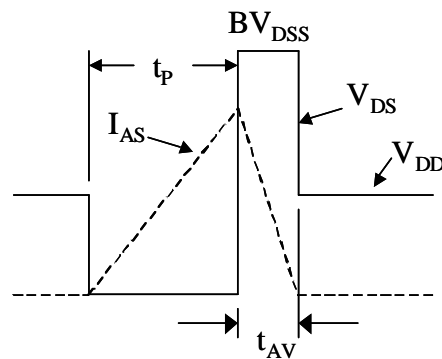


Figure 15. Unclamped Inductive Waveforms

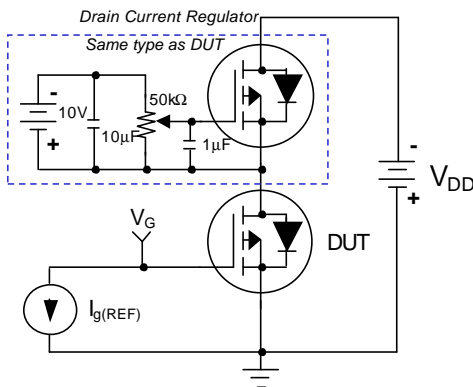


Figure 16. Gate Charge Test Circuit

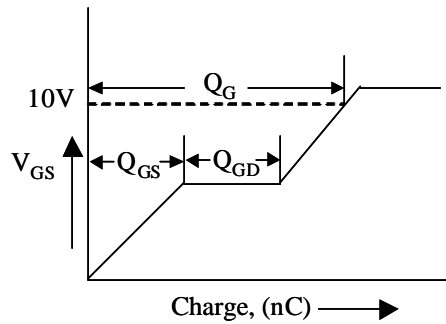


Figure 17. Gate Charge Waveform

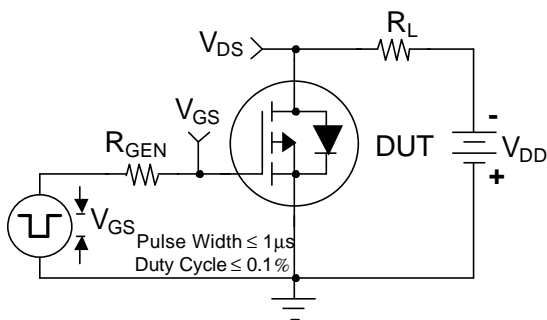


Figure 18. Switching Time Test Circuit

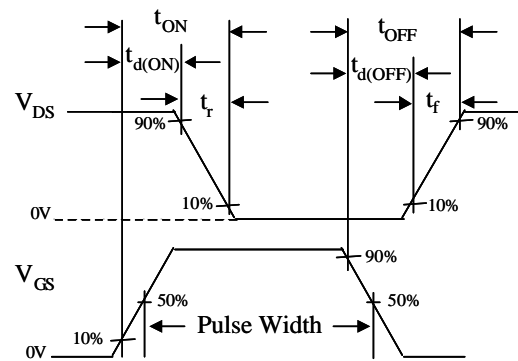
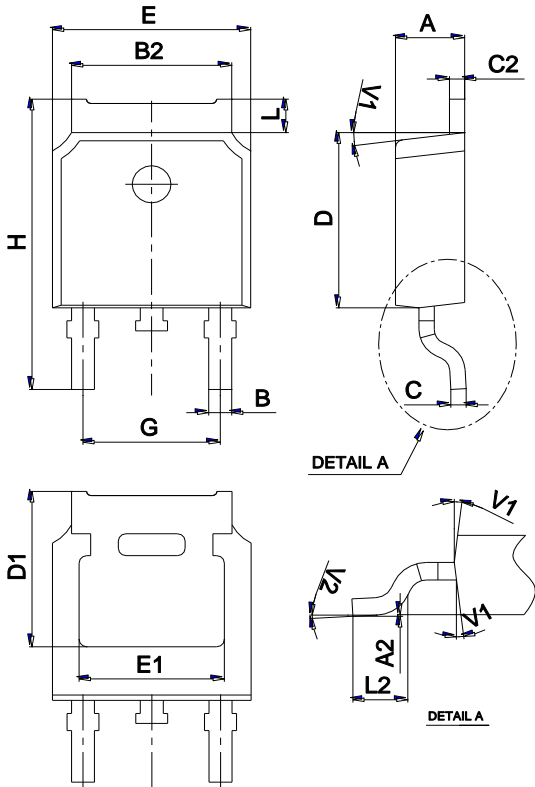


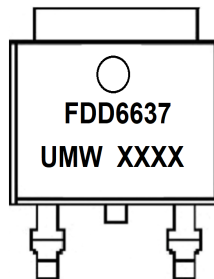
Figure 19. Switching Time Waveforms

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FDD6637	TO-252	2500	Tape and reel



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[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1\\_T0\\_00201](#) [PJMF380N65E1\\_T0\\_00201](#)  
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